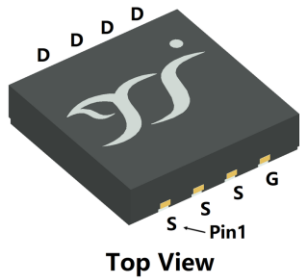
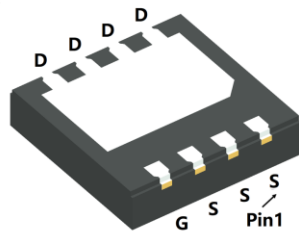




N-Channel Enhancement Mode Field Effect Transistor

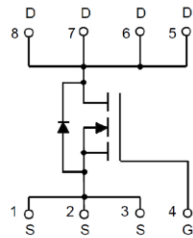


Top View



Bottom View

DFN3333-8L-WF



Product Summary

• V_{DS}	40V
• I_D	99A
• $R_{DS(ON)}$ (at $V_{GS}=10V$)	$<3.3m\Omega$
• $R_{DS(ON)}$ (at $V_{GS}=4.5V$)	$<4.9m\Omega$
• 100% EAS Tested	
• 100% ∇V_{DS} Tested	
• ESD Level(HBM)	H1C

General Description

- Package with side-wettable flanks
- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power switching application
- Uninterruptible power supply
- DC-DC convertor

Limiting Values

Parameter	Conditions		Symbol	Min	Max	Unit
Drain-source Voltage			V_{DS}	-	40	V
Gate-source Voltage			V_{GS}	-20	20	
Continuous Drain Current (Note 1,2)	Steady-State	$T_A=25^{\circ}C, V_{GS}=10V$	I_D	-	16.8	A
		$T_A=100^{\circ}C, V_{GS}=10V$		-	11.8	
Continuous Drain Current (Note 1,3)	Steady-State	$T_C=25^{\circ}C, V_{GS}=10V$, Chip limitation		-	99	
		$T_C=100^{\circ}C, V_{GS}=10V$		-	70	
Pulsed Drain Current	$T_C=25^{\circ}C, t_p \leq 10\mu s$		I_{DM}	-	396	
Maximum Body-Diode Continuous Current	$T_C=25^{\circ}C$		I_S	-	72	
Avalanche energy (non-repetitive)	$T_J=25^{\circ}C, V_G=10V, R_G=25\Omega, L=1mH, I_{AS}=18.8A$		EAS	-	176.7	mJ
Total Power Dissipation (Note 1,2)	Steady-State	$T_A=25^{\circ}C$	P_D	-	2.5	W
		$T_A=100^{\circ}C$		-	1.25	
Total Power Dissipation (Note 1,3)	Steady-State	$T_C=25^{\circ}C$		-	86	
		$T_C=100^{\circ}C$		-	43	
Junction and Storage Temperature Range			T_J, T_{STG}	-55	175	$^{\circ}C$

Thermal Resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	Steady-State	$R_{\theta JA}$	-	60	$^{\circ}C/W$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	-	1.73	

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJQ3D3G04A	F1	Q3D3G04A	5000	10000	100000	13" reel



YJQ3D3G04A

■ Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =1mA, T _j =25℃	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =32V, V _{GS} =0V, T _j =25℃	-	-	1	μA
		V _{DS} =32V, V _{GS} =0V, T _j =100℃	-	-	100	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V, T _j =25℃	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA, T _j =25℃	1.2	1.7	2.4	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A, T _j =25℃	-	2.3	3.3	mΩ
		V _{GS} =4.5V, I _D =10A, T _j =25℃	-	3.3	4.9	
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V, T _j =25℃	-	0.79	1.2	V
Gate Resistance	R _G	f=1MHz, T _j =25℃	-	1.8	-	Ω
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, f=1MHz, T _j =25℃	-	2417	-	pF
Output Capacitance	C _{oss}		-	1040	-	
Reverse Transfer Capacitance	C _{rss}		-	94	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =20V, I _D =20A, T _j =25℃	-	47	-	nC
Gate-Source Charge	Q _{gs}		-	8	-	
Gate-Drain Charge	Q _{gd}		-	13	-	
Reverse Recovery Charge	Q _{rr}	I _F =20A, di/dt=100A/μs, V _{GS} =0V, V _R =20V, T _j =25℃	-	30	-	nC
Reverse Recovery Time	t _{rr}		-	36	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DS} =20V, I _D =20A, R _{GEN} =3Ω, T _j =25℃	-	12	-	ns
Turn-on Rise Time	t _r		-	51	-	
Turn-off Delay Time	t _{D(off)}		-	40	-	
Turn-off Fall Time	t _f		-	27	-	

Note:

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. The value of $R_{\theta JA}$ is measured with the device mounted on the 40mm*40mm*1.1mm single layer FR-4 PCB board with 1 in² pad of 2oz. Copper, in the still air environment with $T_A=25^{\circ}C$. The maximum allowed junction temperature of $175^{\circ}C$. The value in any given application depends on the user's specific board design.
3. Thermal resistance from junction to soldering point (on the exposed drain pad).



YJQ3D3G04A

■ Typical Electrical and Thermal Characteristics Diagrams

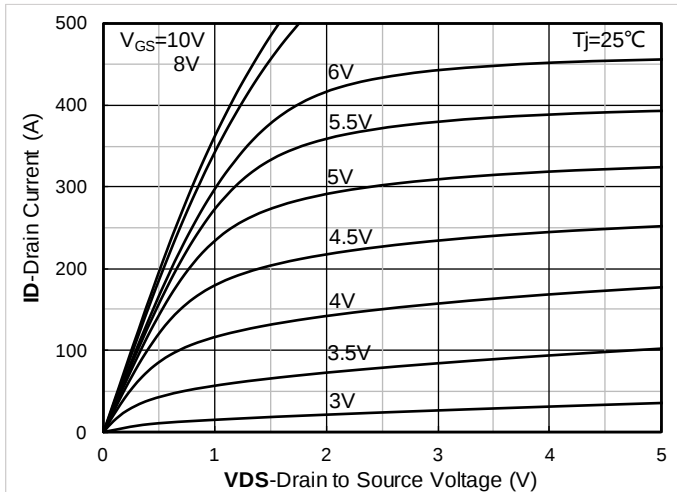


Figure 1. Output Characteristics; typical values

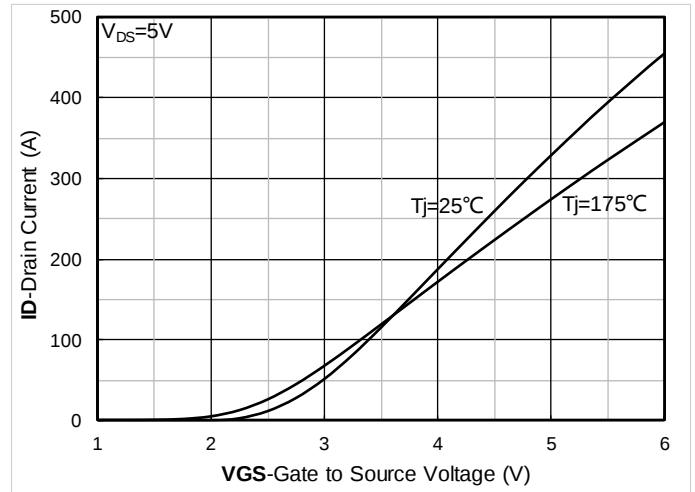


Figure 2. Transfer Characteristics; typical values

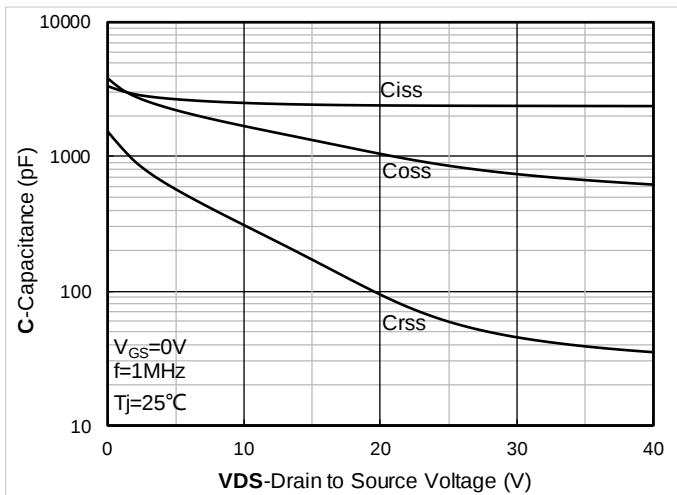


Figure 3. Capacitance Characteristics; typical values

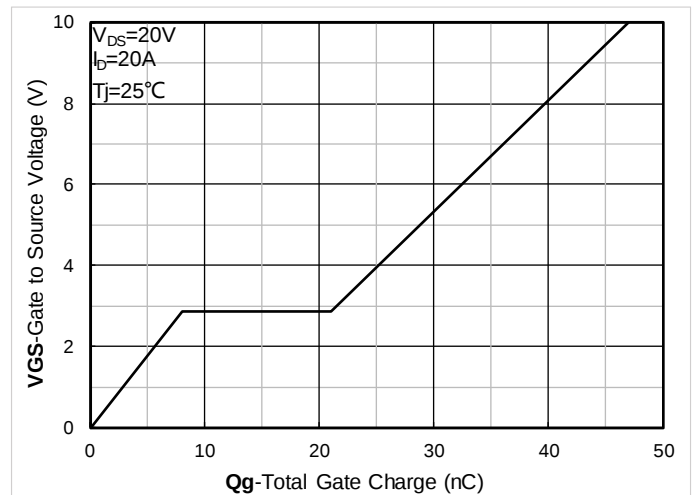


Figure 4. Gate Charge; typical values

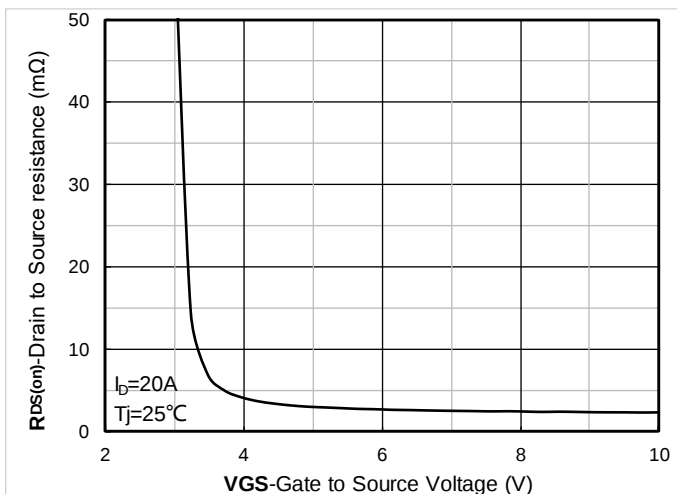


Figure 5. On-Resistance vs. Gate to Source Voltage; typical values

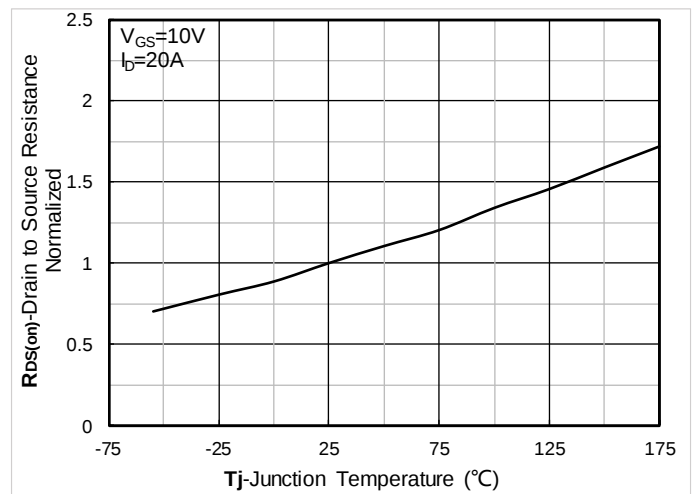


Figure 6. Normalized On-Resistance



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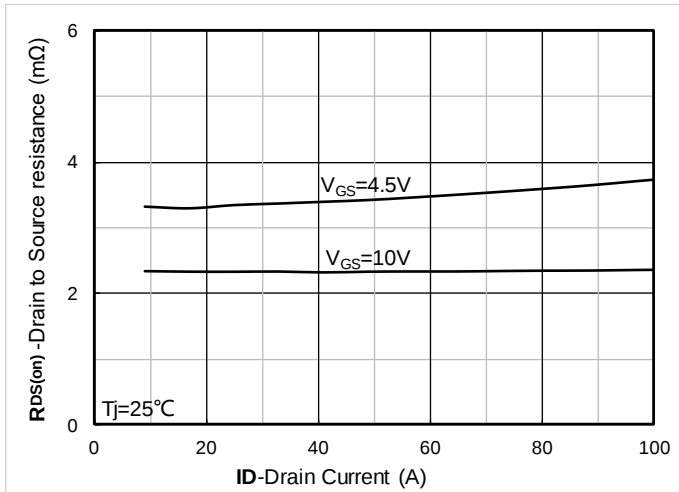


Figure 7. RDS(on) vs. Drain Current; typical values

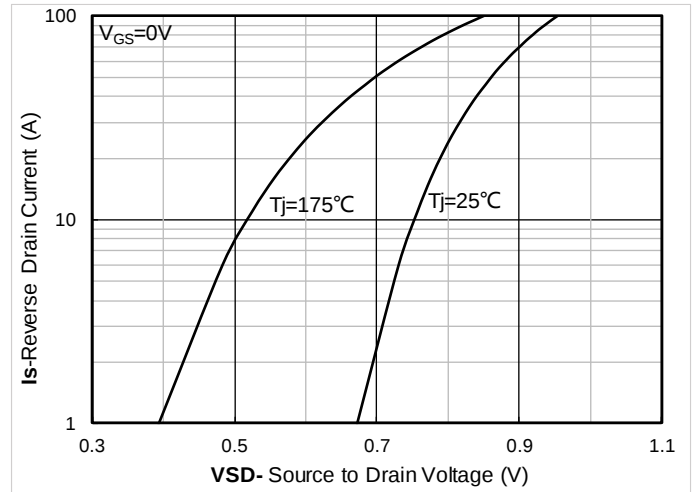


Figure 8. Forward characteristics of reverse diode; typical values

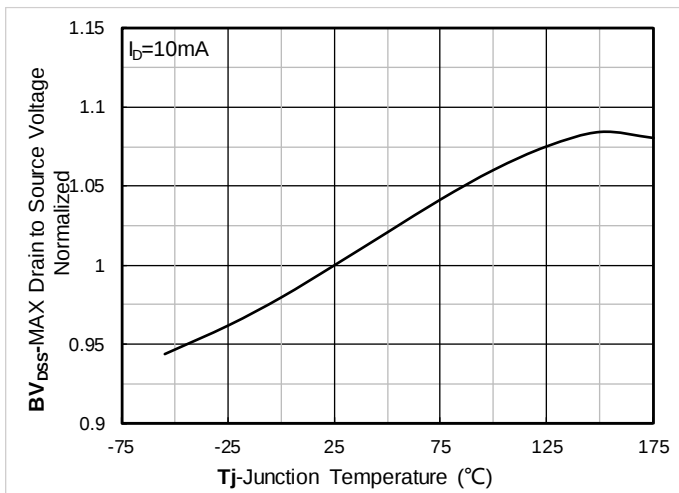


Figure 9. Normalized breakdown voltage

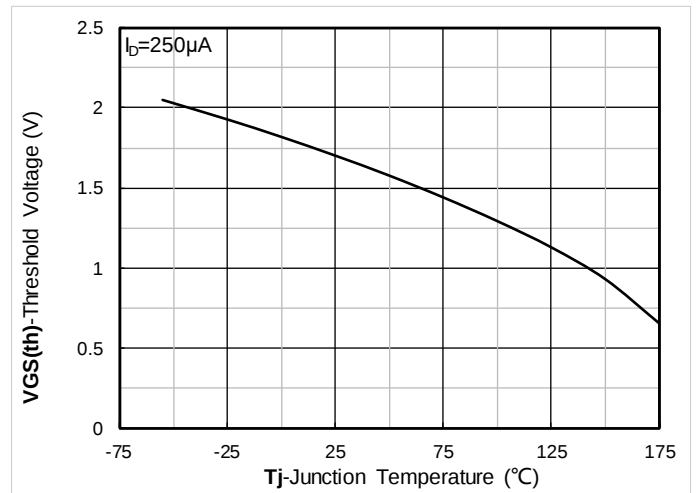


Figure 10. Gate Threshold voltage; typical values

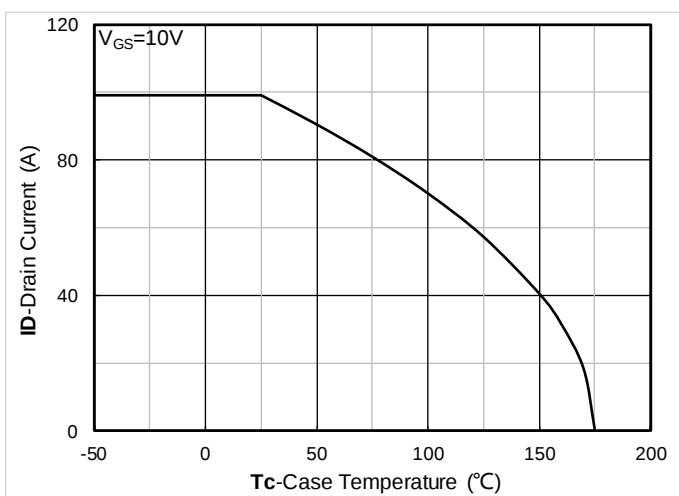


Figure 11. Current dissipation

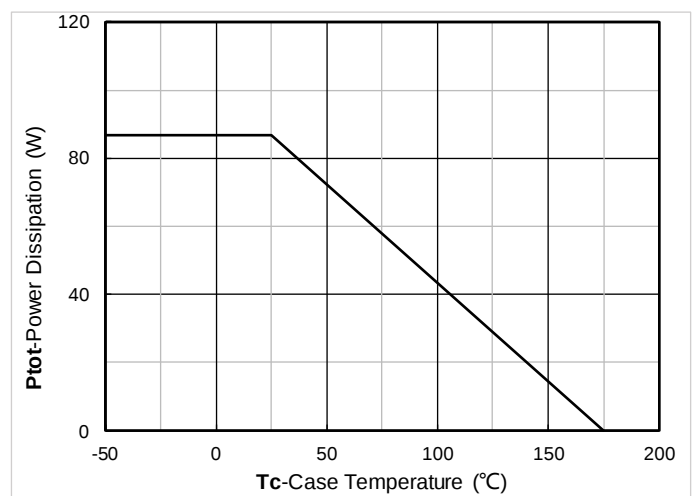


Figure 12. Power dissipation

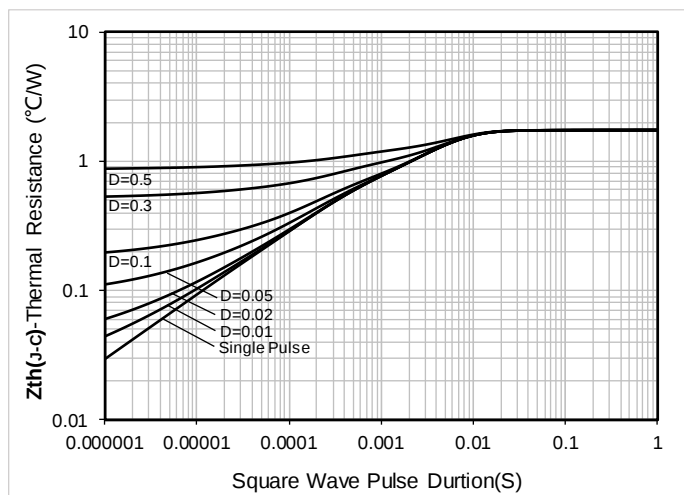


Figure 13. Maximum Transient Thermal Impedance

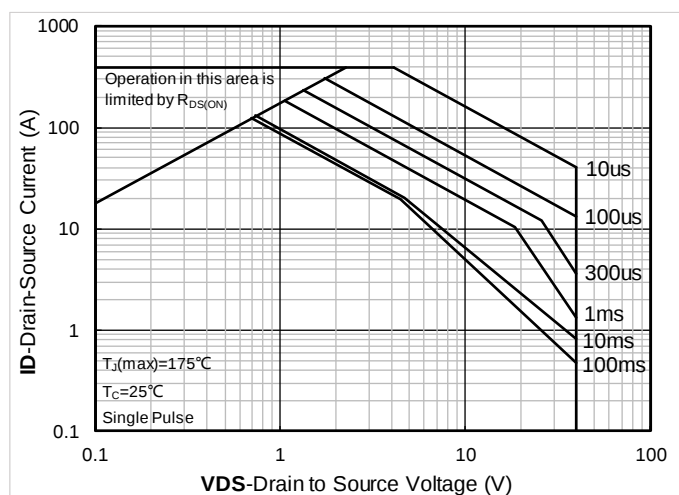
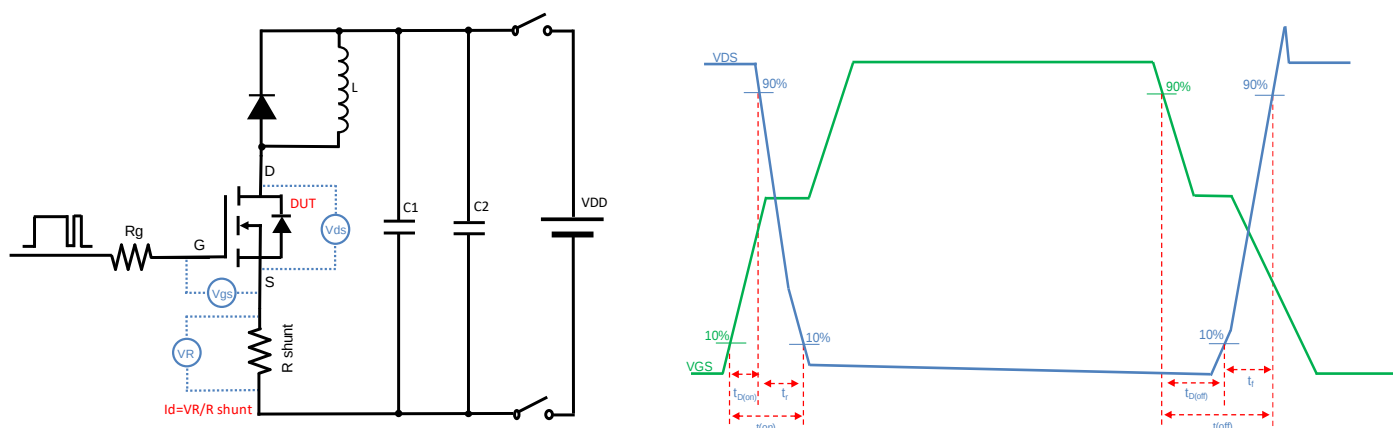
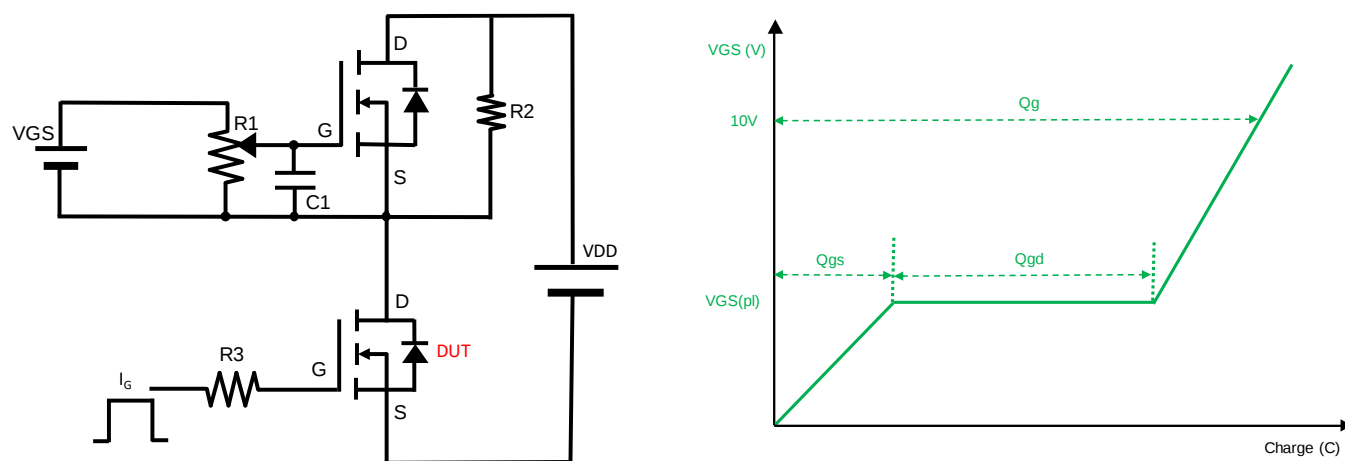
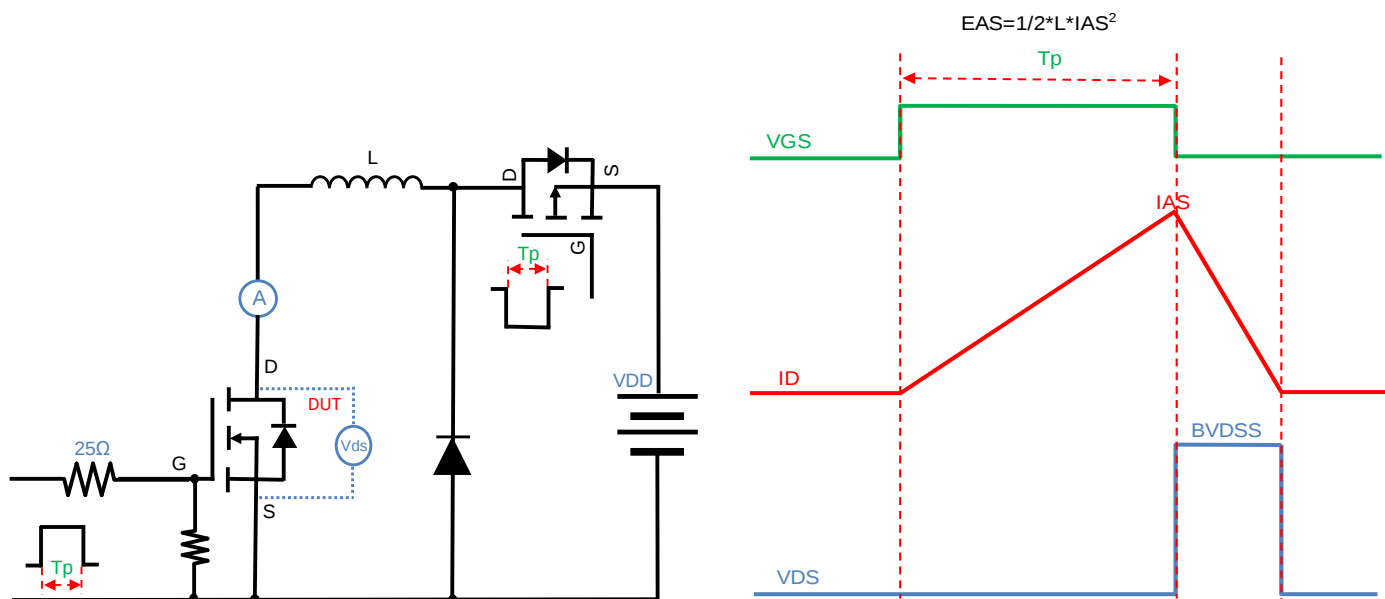


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms



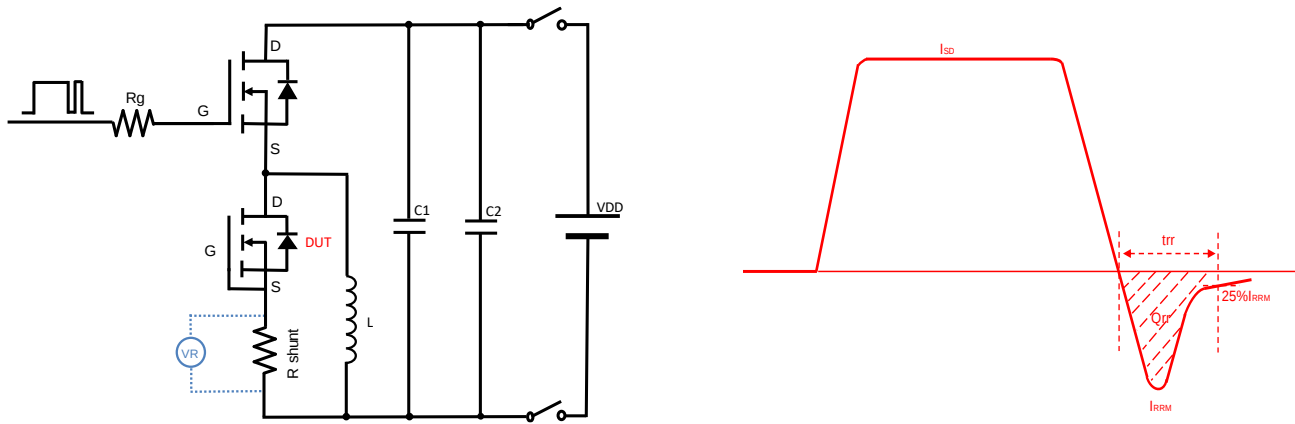
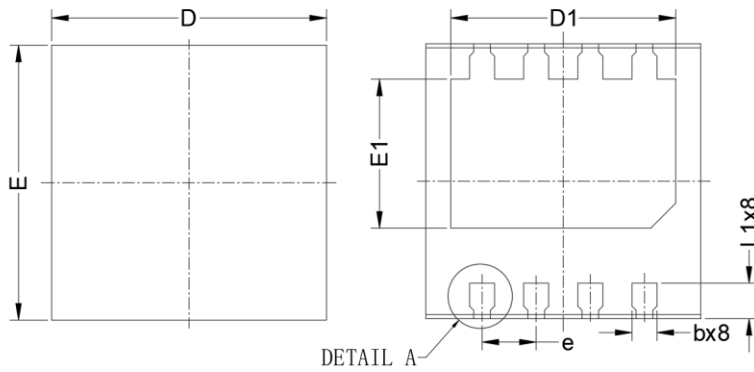


Figure D. Diode Recovery Test Circuit & Waveform



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■ DFN3333-8L-WF Package information



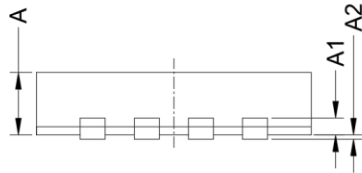
Top View
正面视图

Bottom View
背面视图

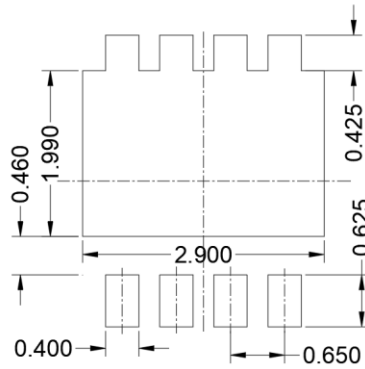
SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	3.30 BSC		
E	3.30 BSC		
A	0.70	0.75	0.80
A1	0.203 BSC		
A2			0.10
D1	2.60	2.70	2.80
E1	1.69	1.79	1.89
L1	0.325	0.425	0.525
b	0.20	0.30	0.40
e	0.65 BSC		

Note:

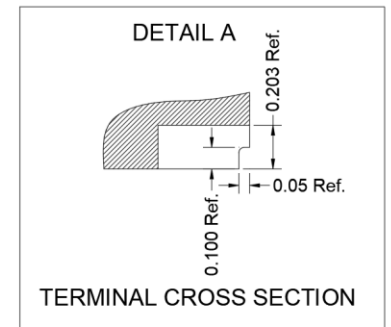
1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.10 mm.
3. The pad layout is for reference purposes only.



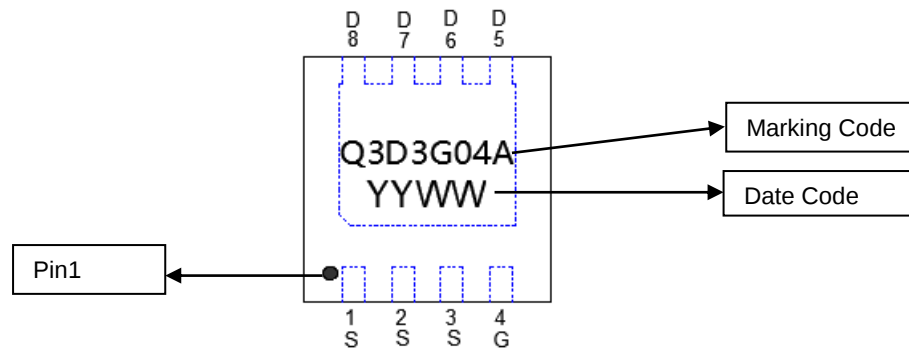
Side View
侧面视图



Suggested Solder Pad Layout
Top View



■ Marking Information



Note:

1. All marking is at middle of the product body
2. All marking is in laser printing
3. Q3D3G04A is marking code, YYWW is date code, "YY" is year, "WW" is week
4. Body color: Black



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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

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